onsemi

Dual Transistor -Power Management

NPN/PNP Dual (Complementary)

EMF18XV6T5

Features

- Low V_{CE(SAT)}, <0.5 V
- These are Pb-Free Devices

MAXIMUM RATINGS

QI		
		Rati

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	Ι _C	100	mAdc

Q2

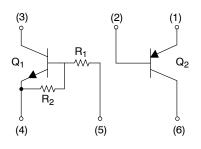
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-60	V
Collector – Base Voltage	V _{CBO}	-50	V
Emitter – Base Voltage	V _{EBO}	-6.0	V
Collector Current – Continuous	۱ _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Мах	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	357 (Note 1) 2.9	mW mW/°C
Derate above 25 0		(Note 1)	11100/ 0
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	350 (Note 1)	°C/W
Characteristic			
(Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$	PD	500 (Note1)	mW
Derate above 25°C		4.0 (Note 1)	mW/°C
Thermal Resistance,	$R_{ hetaJA}$	250	°C/W
Junction-to-Ambient		(Note 1)	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad.





SOT-563 CASE 463A PLASTIC

MARKING DIAGRAM



UV = Specific Device Code M = Date Code

= Date Code
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
EMF18XV6T5G	SOT–563 (Pb–Free)	8000/Tape & Reel
EMF18XV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

EMF18XV6T5

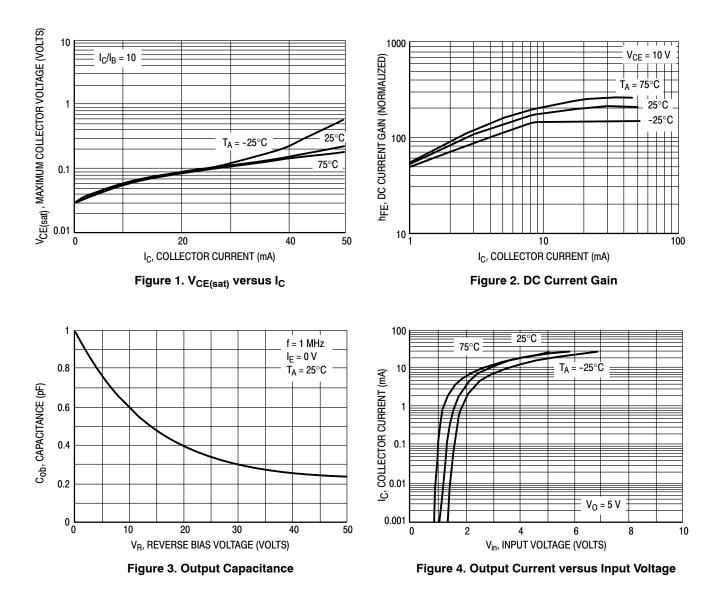
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$) (Note 2)

Characteristic	Symbol	Min	Тур	Мах	Unit
Q1: NPN					
Collector-Base Cutoff Current (V _{CB} = 50 V, $I_E = 0$)	I _{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I_C = 0)	I _{EBO}	-	-	0.1	mAdc
Collector-Base Breakdown Voltage ($I_C = 10 \ \mu A$, $I_E = 0$)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	-	-	Vdc
DC Current Gain (V _{CE} = 10 V, I_C = 5.0 mA)	h _{FE}	80	140	-	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)	V _{CE(sat)}	-	-	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 k\Omega)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 k\Omega)	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	
Q2: PNP	•	•			
Collector-Base Breakdown Voltage (I _C = $-50 \ \mu$ Adc, I _E = 0)	V _{(BR)CBO}	-60	-	-	Vdc
Collector-Emitter Breakdown Voltage ($I_{C} = -1.0 \text{ mAdc}, I_{B} = 0$)	V _{(BR)CEO}	-50	-	-	Vdc
Emitter-Base Breakdown Voltage (I _E = $-50 \ \mu$ Adc, I _E = 0)	V _{(BR)EBO}	-6.0	-	-	Vdc
Collector-Base Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	-	-	-0.5	nA
Emitter-Base Cutoff Current ($V_{EB} = -5.0 \text{ Vdc}, I_B = 0$)	I _{EBO}	-	-	-0.5	μA
Collector-Emitter Saturation Voltage (Note 4) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)	V _{CE(sat)}	-	-	-0.5	Vdc
DC Current Gain (Note 4) (V_{CE} = -6.0 Vdc, I_C = -1.0 mAdc)	h _{FE}	120	-	560	-
Transition Frequency (V _{CE} = -12 Vdc, I _C = -2.0 mAdc, f = 30 MHz)	f _T	-	140	-	MHz
Output Capacitance (V_{CB} = -12 Vdc, I_E = 0 Adc, f = 1.0 MHz)	C _{OB}	-	3.5	-	pF

3. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint. 4. Pulse Test: Pulse Width \leq 300 µs, D.C. \leq 2%.

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TYPICAL ELECTRICAL CHARACTERISTICS — Q1, NPN



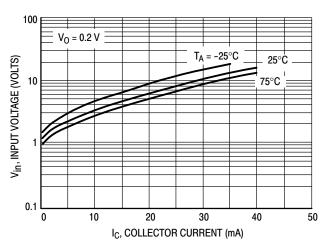
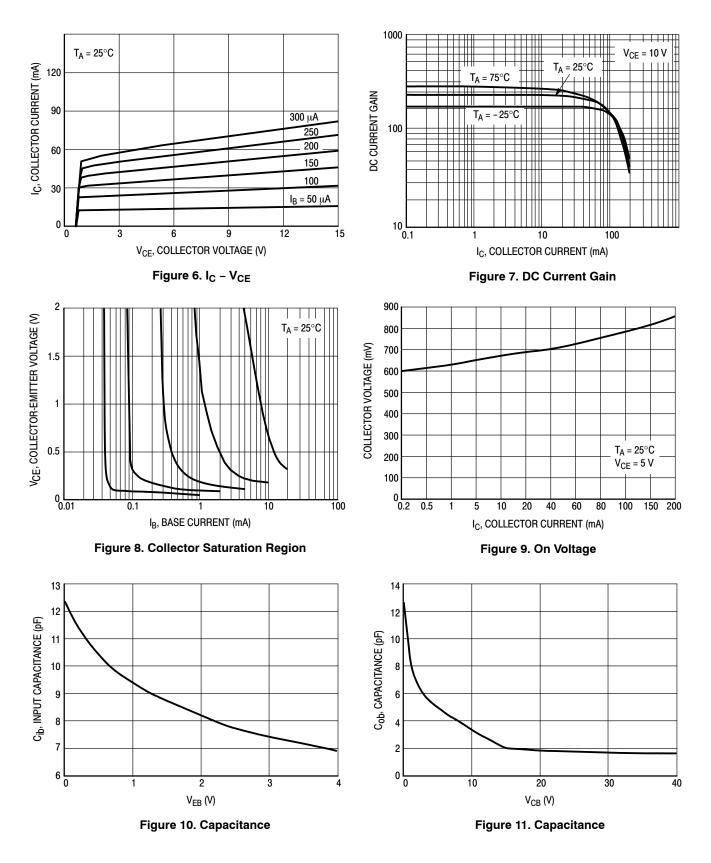


Figure 5. Input Voltage versus Output Current

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TYPICAL ELECTRICAL CHARACTERISTICS – Q2, PNP



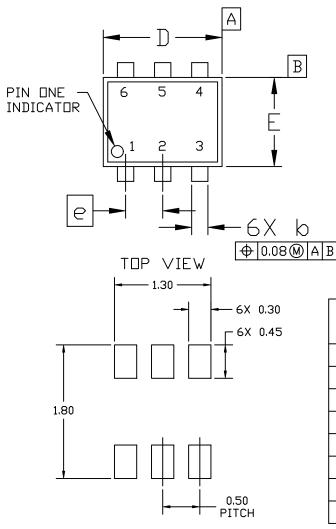




SOT-563, 6 LEAD CASE 463A ISSUE H

DATE 26 JAN 2021

- NDTES: DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 1. CONTROLLING DIMENSION: MILLIMETERS 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH З. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS. THICKNESS OF BASE MATERIAL.



RECOMMENDED MOUNTING FOOTPRINT* For additional information on our Pb-Free ж strategy and soldering details, please download

the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SIDE VIEW

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
А	0.50	0.55	0.60	
b	0.17	0.22	0.27	
С	0.08	0.13	0.18	
D	1.50	1.60	1.70	
E	1.10	1.20	1.30	
е	0.50 BSC			
L	0.10	0.20	0.30	
Η _E	1.50	1.60	1.70	

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STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHIDE 1
2. BASE 1	2. EMITTER 2	2. CATHIDE 1
3. COLLECTOR 2	3. BASE 2	3. ANUDE/ANUDE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHIDE 2
5. BASE 2	5. BASE 1	5. CATHIDE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANUDE/ANUDE 1
STYLE 4:	STYLE 5:	STYLE 6;
PIN 1. COLLECTOR	PIN 1. CATHEDE	PIN 1. CATHODE
2. COLLECTOR	2. CATHEDE	2. ANODE
3. BASE	3. ANEDE	3. CATHODE
4. EMITTER	4. ANEDE	4. CATHODE
5. COLLECTOR	5. CATHEDE	5. CATHODE
6. COLLECTOR	6. CATHEDE	6. CATHODE
STYLE 7:	STYLE 8:	STYLE 9:
PIN 1. CATHEDE	PIN 1. DRAIN	PIN 1. SDURCE 1
2. ANEDE	2. DRAIN	2. GATE 1
3. CATHEDE	3. GATE	3. DRAIN 2
4. CATHEDE	4. SDURCE	4. SDURCE 2
5. ANEDE	5. DRAIN	5. GATE 2
6. CATHEDE	6. DRAIN	6. DRAIN 1
STYLE 10: PIN 1. CATHEDE 1 2. N/C 3. CATHEDE 2 4. ANEDE 2 5. N/C	STYLE 11: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1	

5. BASE 1 6. COLLECTOR 2

6. ANDDE 1

DATE 26 JAN 2021

GENERIC **MARKING DIAGRAM***



XX = Specific Device Code

M = Month Code .

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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